

isc N-Channel MOSFET Transistor

2SK1631

DESCRIPTION

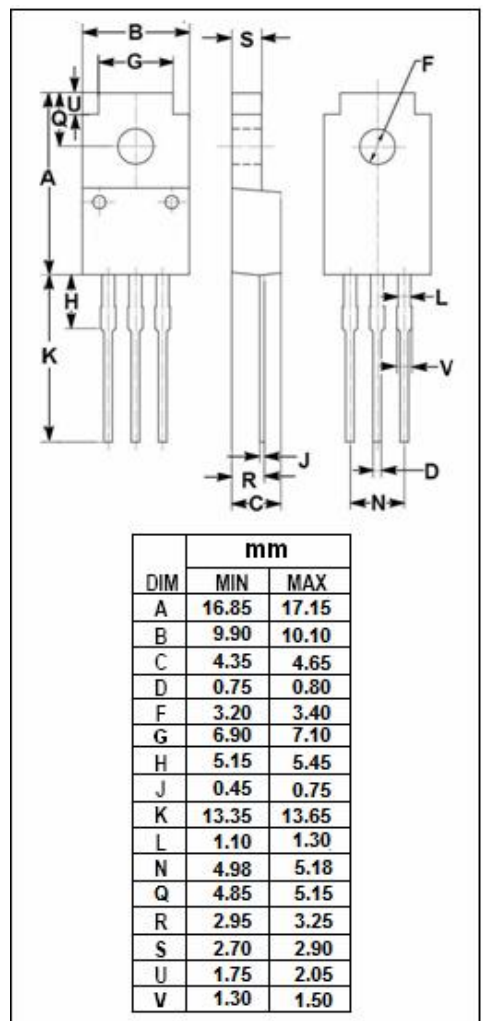
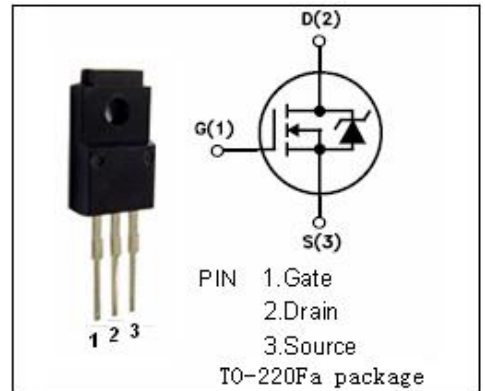
- Drain Current  $-I_D = 3A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 700V(\text{Min})$

APPLICATIONS

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

SYMBOL	ARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS} = 0$ )	700	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $TC = 25^\circ C$	3	A
$P_{tot}$	Total Dissipation@ $TC = 25^\circ C$	35	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc N-Channel Mosfet Transistor****2SK1631****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 10mA	700			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =10 V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.0	3.0	4.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =1.5A			4.4	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			± 100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =700V; V <sub>GS</sub> = 0			500	uA